

# DSC2002

## Silicon NPN epitaxial planar type

For general amplification

Complementary to DSA2002

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Eco-friendly Halogen-free package

### ■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	500	mA
Peak collector current	$I_{CP}$	1	A
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Package

- Code  
Mini3-G3-B-B
- Pin Name
  1. Base
  2. Emitter
  3. Collector

### ■ Marking Symbol: C2

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{V}, I_E = 0$			0.1	$\mu\text{A}$
Forward current transfer ratio *1	$h_{FE1}$ *2	$V_{CE} = 10 \text{V}, I_C = 150 \text{mA}$	120		340	—
	$h_{FE2}$	$V_{CE} = 10 \text{V}, I_C = 500 \text{mA}$	40			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$		0.1	0.6	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{V}, I_C = 50 \text{mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{V}, I_E = 0, f = 1 \text{MHz}$		4.8	15	pF

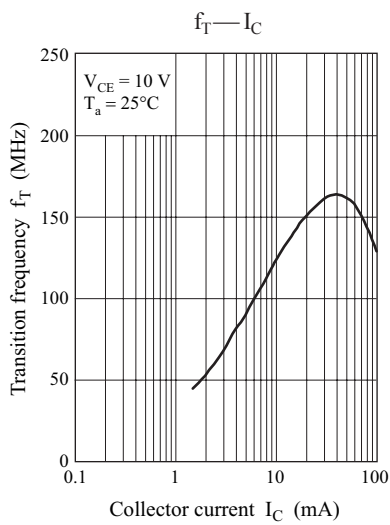
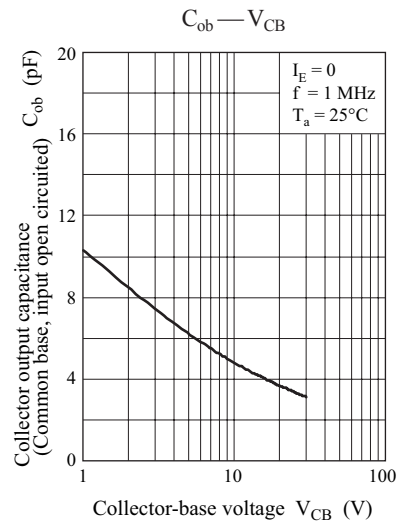
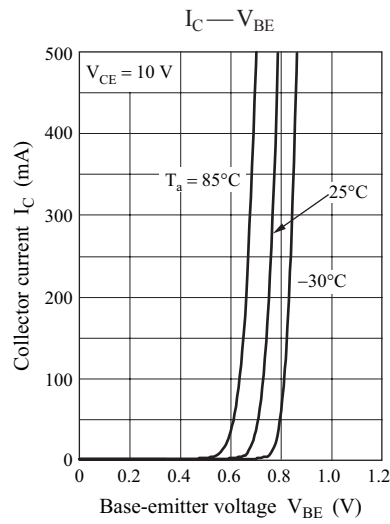
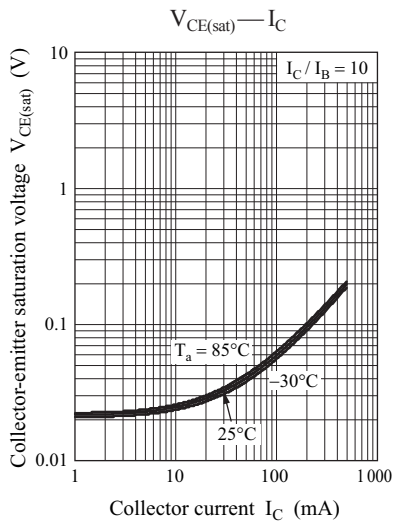
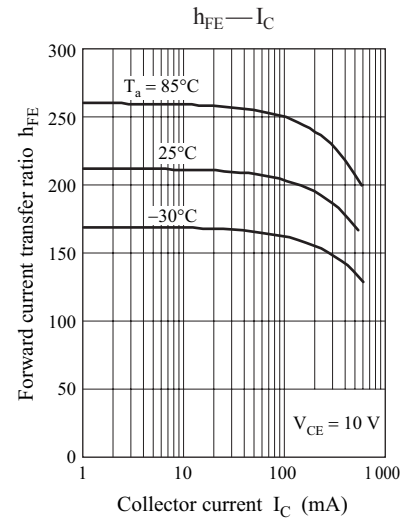
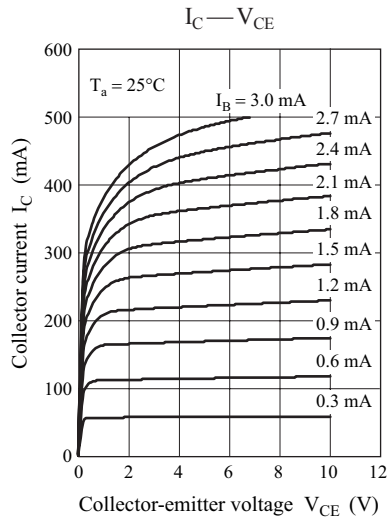
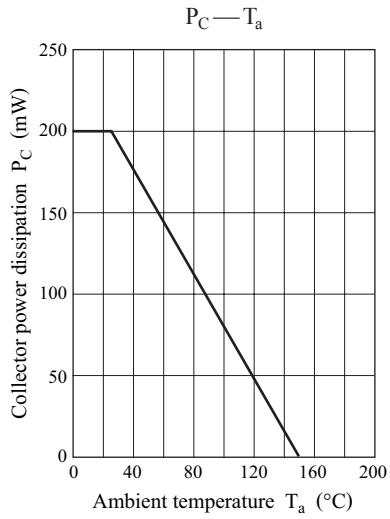
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

\*2: Rank classification

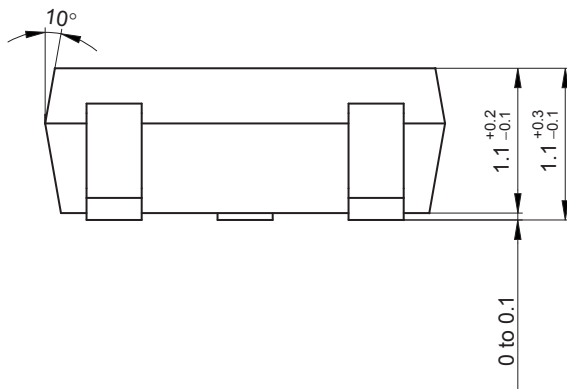
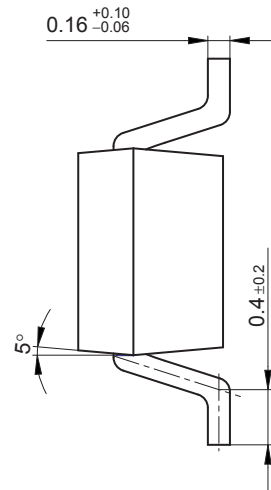
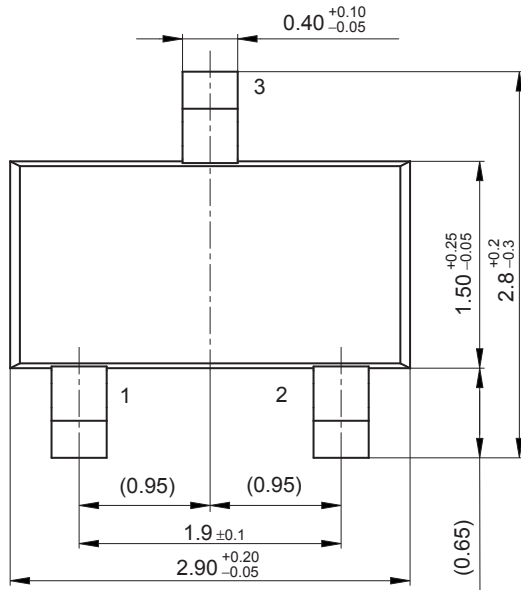
Code	R	S	0
Rank	R	S	No-rank
$h_{FE}$	120 to 240	170 to 340	120 to 340
Marking Symbol	C2R	C2S	C2

Product of no-rank is not classified and have no marking symbol for rank.



Mini3-G3-B-B

Unit: mm



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